

### FEATURES

- ❑ 20 ns Multiply-Accumulate Time
- ❑ Replaces TRW TMC2210, Cypress CY7C510, IDT 7210L, and AMD Am29510
- ❑ Two's Complement or Unsigned Operands
- ❑ Accumulator Performs Preload, Accumulate, and Subtract
- ❑ Three-State Outputs
- ❑ DECC SMD No. 5962-88733
- ❑ Available 100% Screened to MIL-STD-883, Class B
- ❑ Package Styles Available:
  - 64-pin Sidebraze, Hermetic DIP
  - 68-pin Ceramic PGA
  - 68-pin Plastic LCC, J-Lead
  - 68-pin Ceramic LCC

### DESCRIPTION

The LMA1010 and LMA2010 are high-speed, low power 16-bit multiplier-accumulators. The LMA1010 and LMA2010 are functionally identical; they differ only in packaging. Full military ambient temperature range operation is achieved with advanced CMOS technology.

The LMA1010 and LMA2010 produce the 32-bit product of two 16-bit numbers. The results of a series of multiplications may be accumulated to form the sum of products. Accumulation is performed to 35-bit precision with the multiplier product sign extended as appropriate.

Data present at the A and B input registers is latched on the rising edges

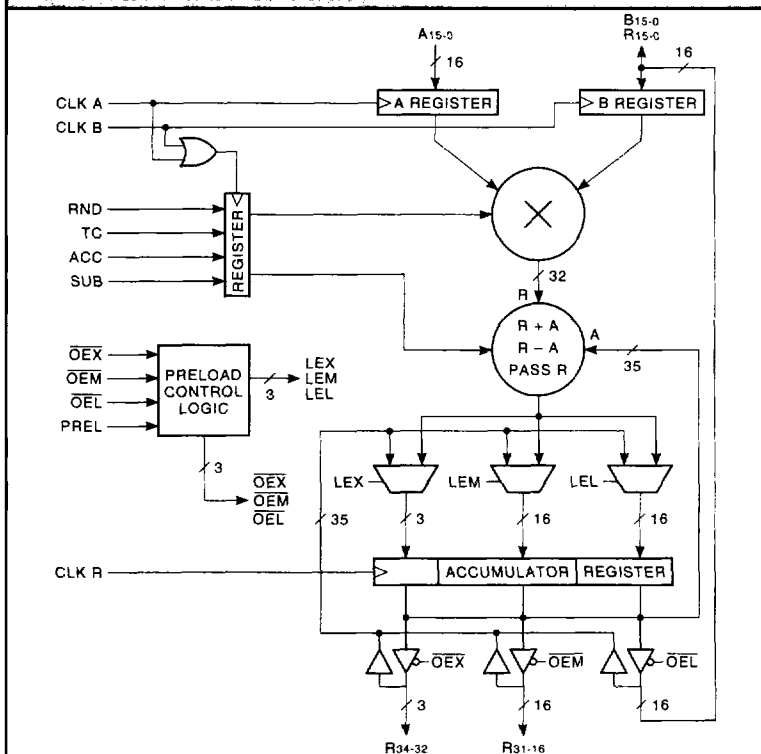
of CLK A and CLK B respectively. RND, TC, ACC, and SUB controls are latched on the rising edge of the logical OR of CLK A and CLK B. TC specifies the input as two's complement (TC HIGH) or unsigned magnitude (TC LOW). RND, when HIGH, adds '1' to the most significant bit position of the least significant half of the product. Subsequent truncation of the 16 least significant bits produces a result correctly rounded to 16-bit precision.

ACC and SUB control accumulator operation. ACC HIGH results in addition of the multiplier product and the accumulator contents, with the result stored in the accumulator register on the rising edge of CLK R. ACC and SUB HIGH results in subtraction of the accumulator contents from the multiplier product, with the result stored in the accumulator register. With ACC LOW, no accumulation occurs and the next product is loaded directly into the accumulator register.

The LMA1010/2010 output register (accumulator register) is divided into three independently controlled sections. The least significant result (LSR) and most significant result (MSR) registers are 16 bits in length. The extended result register (XTR) is 3 bits long. The output signals R15-0 and input signals B15-0 share the same bidirectional pins.

Each output register has an independent output enable control. In addition to providing three-state control of the output buffers, when OEX, OEM, or OEL are HIGH and PREL is HIGH, data can be preloaded via the bidirectional output pins into the respective output registers. Data present on the output pins is latched on the rising edge of CLK R. The interrelation of PREL and the enable controls is summarized in Table 1.

### LMA1010/2010 BLOCK DIAGRAM

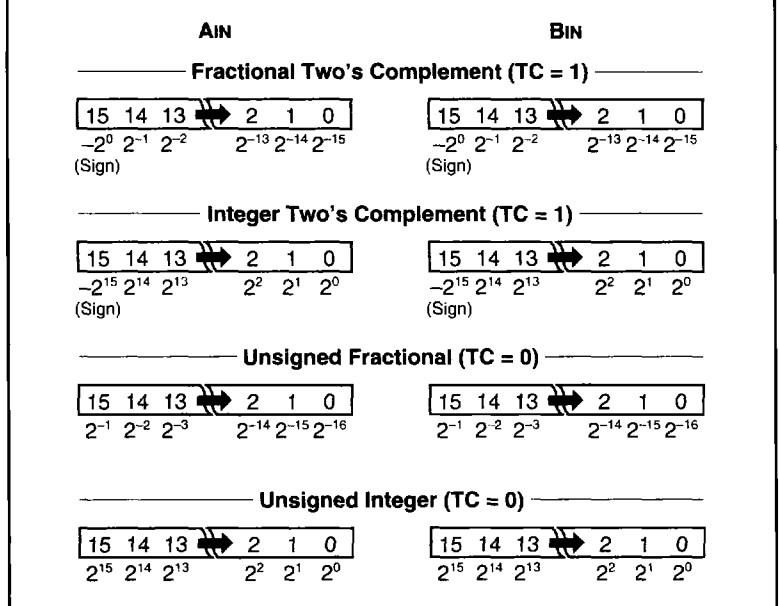
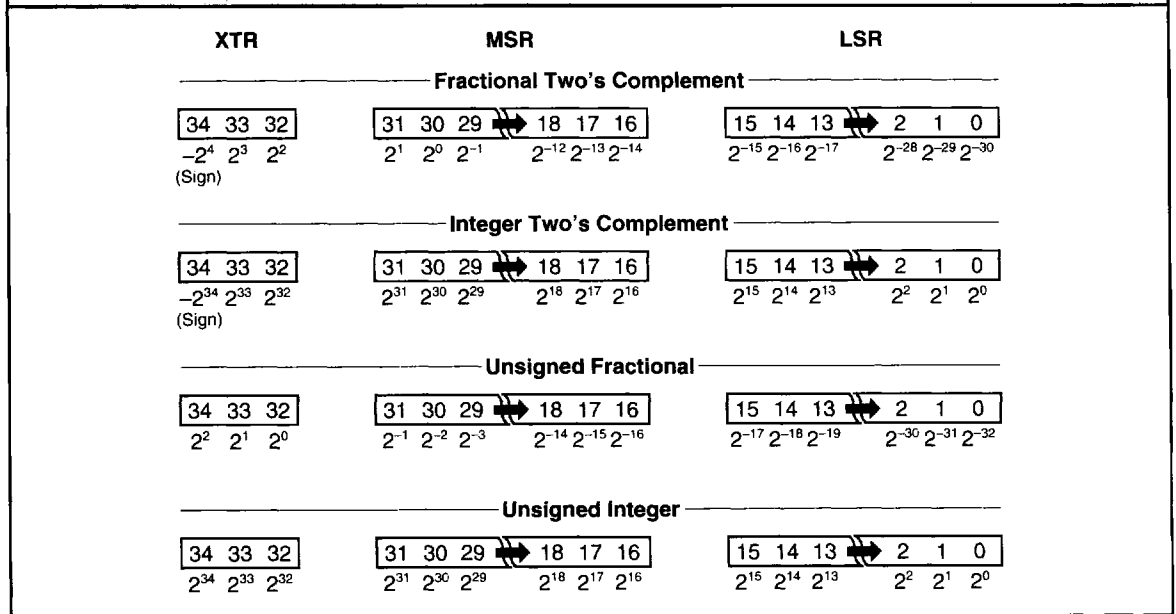


## 16 x 16-bit Multiplier-Accumulator

**TABLE 1. PRELOAD TRUTH TABLE**

PREL	OEX	OEM	OEL	XTR	MSR	LSR
L	L	L	L	OUT	OUT	OUT
L	L	L	H	OUT	OUT	Z
L	L	H	L	OUT	Z	OUT
L	L	H	H	OUT	Z	Z
L	H	L	L	Z	OUT	OUT
L	H	L	H	Z	OUT	Z
L	H	H	L	Z	Z	OUT
L	H	H	H	Z	Z	Z
H	L	L	L	Z	Z	Z
H	L	L	H	Z	Z	PREL
H	L	H	L	Z	PREL	Z
H	L	H	H	Z	PREL	PREL
H	H	L	L	PREL	Z	Z
H	H	L	H	PREL	Z	PREL
H	H	H	L	PREL	PREL	Z
H	H	H	H	PREL	PREL	PREL

PREL = Preload data to appropriate register  
 OUT = Register available on output pins  
 Z = High impedance state

**FIGURE 1A. INPUT FORMATS**

**FIGURE 1B. OUTPUT FORMATS**


**16 x 16-bit Multiplier-Accumulator**

**MAXIMUM RATINGS** Above which useful life may be impaired (Notes 1, 2, 3, 8)

Storage temperature .....	-65°C to +150°C
Operating ambient temperature .....	-55°C to +125°C
VCC supply voltage with respect to ground .....	-0.5 V to +7.0 V
Input signal with respect to ground .....	-3.0 V to +7.0 V
Signal applied to high impedance output .....	-3.0 V to +7.0 V
Output current into low outputs .....	25 mA
Latchup current .....	> 400 mA

**OPERATING CONDITIONS** To meet specified electrical and switching characteristics

Mode	Temperature Range (Ambient)	Supply Voltage
Active Operation, Commercial	0°C to +70°C	4.75 V ≤ VCC ≤ 5.25 V
Active Operation, Military	-55°C to +125°C	4.50 V ≤ VCC ≤ 5.50 V

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**ELECTRICAL CHARACTERISTICS** Over Operating Conditions (Note 4)

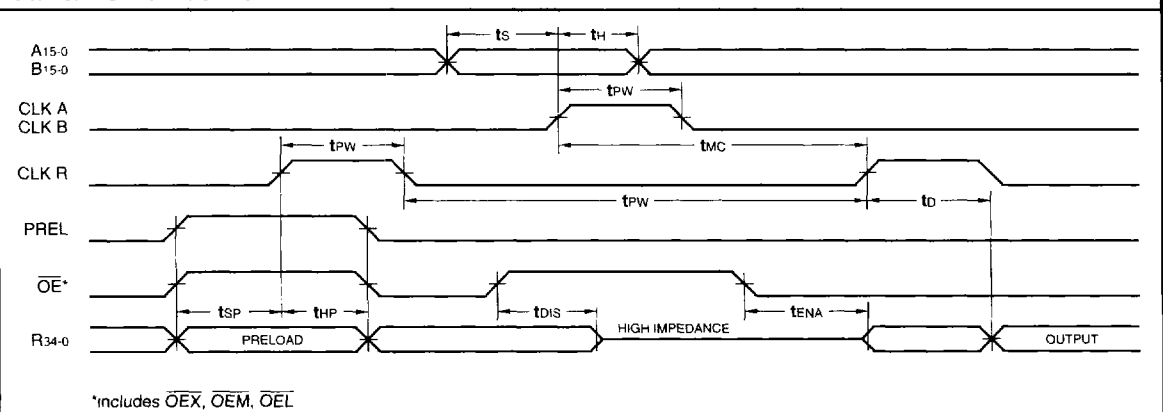
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V <sub>OH</sub>	Output High Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = -2.0 mA	2.4			V
V <sub>OL</sub>	Output Low Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA			0.5	V
V <sub>IH</sub>	Input High Voltage		2.0		V <sub>CC</sub>	V
V <sub>IL</sub>	Input Low Voltage	(Note 3)	0.0		0.8	V
I <sub>Ix</sub>	Input Current	Ground ≤ V <sub>IN</sub> ≤ V <sub>CC</sub> (Note 12)			±20	µA
I <sub>OZ</sub>	Output Leakage Current	Ground ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub> (Note 12)			±20	µA
I <sub>CC1</sub>	VCC Current, Dynamic	(Notes 5, 6)		12	25	mA
I <sub>CC2</sub>	VCC Current, Quiescent	(Note 7)			1.0	mA

**SWITCHING CHARACTERISTICS**
**COMMERCIAL OPERATING RANGE (0°C to +70°C) Notes 9, 10 (ns)**

Symbol		Parameter		LMA1010/2010-											
				65		55		45		35		25		20	
				Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
t <sub>MC</sub>	Clocked Multiply Time		65		55		45		35		25		20		
t <sub>PW</sub>	Clock Pulse Width	15		15		15		10		10		9			
t <sub>S</sub>	Input Register Setup Time	15		15		12		12		12		10			
t <sub>H</sub>	Input Register Hold Time	2		2		2		2		2		2			
t <sub>SP</sub>	Preload Setup Time	15		15		12		12		12		10			
t <sub>HP</sub>	Preload Hold Time	2		2		2		2		2		2			
t <sub>D</sub>	Output Delay		30		25		25		25		20		18		
t <sub>ENA</sub>	Three-State Output Enable Delay (Note 11)		30		30		25		25		20		18		
t <sub>DIS</sub>	Three-State Output Disable Delay (Note 11)		30		25		25		25		20		18		

**MILITARY OPERATING RANGE (-55°C to +125°C) Notes 9, 10 (ns)**

Symbol		Parameter		LMA1010/2010-											
				75		65		55		40		30		25	
				Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
t <sub>MC</sub>	Clocked Multiply Time		75		65		55		40		30		25		
t <sub>PW</sub>	Clock Pulse Width	20		15		15		15		10		10			
t <sub>S</sub>	Input Register Setup Time	20		15		15		15		12		12			
t <sub>H</sub>	Input Register Hold Time	2		2		2		2		2		2			
t <sub>SP</sub>	Preload Setup Time	20		15		15		15		12		12			
t <sub>HP</sub>	Preload Hold Time	2		2		2		2		2		2			
t <sub>D</sub>	Output Delay		35		30		30		25		20		20		
t <sub>ENA</sub>	Three-State Output Enable Delay (Note 11)		35		30		30		25		20		20		
t <sub>DIS</sub>	Three-State Output Disable Delay (Note 11)		35		25		25		25		20		20		

**SWITCHING WAVEFORMS**


### NOTES

1. Maximum Ratings indicate stress specifications only. Functional operation of these products at values beyond those indicated in the Operating Conditions table is not implied. Exposure to maximum rating conditions for extended periods may affect reliability.

2. The products described by this specification include internal circuitry designed to protect the chip from damaging substrate injection currents and accumulations of static charge. Nevertheless, conventional precautions should be observed during storage, handling, and use of these circuits in order to avoid exposure to excessive electrical stress values.

3. This device provides hard clamping of transient undershoot and overshoot. Input levels below ground or above VCC will be clamped beginning at  $-0.6\text{ V}$  and  $V_{CC} + 0.6\text{ V}$ . The device can withstand indefinite operation with inputs in the range of  $-0.5\text{ V}$  to  $+7.0\text{ V}$ . Device operation will not be adversely affected, however, input current levels will be well in excess of 100 mA.

4. Actual test conditions may vary from those designated but operation is guaranteed as specified.

5. Supply current for a given application can be accurately approximated by:

$$NCV^2F$$

where

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- N = total number of device outputs
- C = capacitive load per output
- V = supply voltage
- F = clock frequency

6. Tested with all outputs changing every cycle and no load, at a 5 MHz clock rate.

7. Tested with all inputs within 0.1 V of VCC or Ground, no load.

8. These parameters are guaranteed but not 100% tested.

9. AC specifications are tested with input transition times less than 3 ns, output reference levels of 1.5 V (except tDIS test), and input levels of nominally 0 to 3.0 V. Output loading may be a resistive divider which provides for specified IOH and IOL at an output voltage of VOH min and VOL max respectively. Alternatively, a diode bridge with upper and lower current sources of IOH and IOL respectively, and a balancing voltage of 1.5 V may be used. Parasitic capacitance is 30 pF minimum, and may be distributed.

This device has high-speed outputs capable of large instantaneous current pulses and fast turn-on/turn-off times. As a result, care must be exercised in the testing of this device. The following measures are recommended:

a. A 0.1  $\mu\text{F}$  ceramic capacitor should be installed between VCC and Ground leads as close to the Device Under Test (DUT) as possible. Similar capacitors should be installed between device VCC and the tester common, and device ground and tester common.

b. Ground and VCC supply planes must be brought directly to the DUT socket or contactor fingers.

c. Input voltages should be adjusted to compensate for inductive ground and VCC noise to maintain required DUT input levels relative to the DUT ground pin.

10. Each parameter is shown as a minimum or maximum value. Input requirements are specified from the point of view of the external system driving the chip. Setup time, for example, is specified as a minimum since the external system must supply at least that much time to meet the worst-case requirements of all parts. Responses from the internal circuitry are specified from the point of view of the device. Output delay, for example, is specified as a maximum since worst-case operation of any device always provides data within that time.

11. For the tENA test, the transition is measured to the 1.5 V crossing point with datasheet loads. For the tDIS test, the transition is measured to the  $\pm 200\text{ mV}$  level from the measured steady-state output voltage with  $\pm 10\text{ mA}$  loads. The balancing voltage, VTH, is set at 3.5 V for Z-to-0 and 0-to-Z tests, and set at 0 V for Z-to-1 and 1-to-Z tests.

12. These parameters are only tested at the high temperature extreme, which is the worst case for leakage current.

FIGURE A. OUTPUT LOADING CIRCUIT

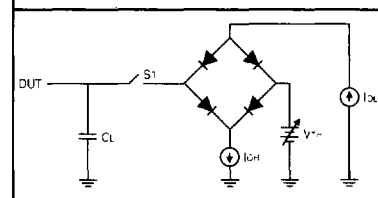
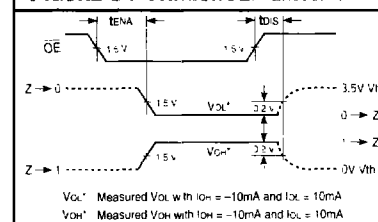


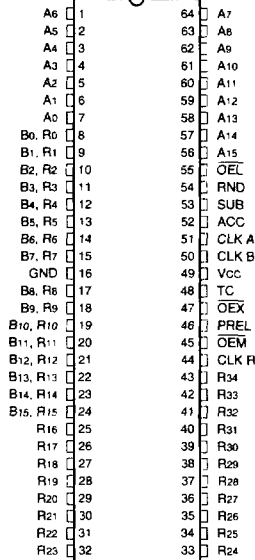
FIGURE B. THRESHOLD LEVELS



## 16 x 16-bit Multiplier-Accumulator

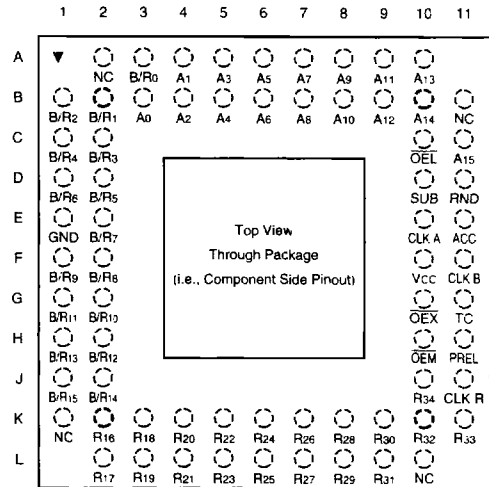
### LMA1010 — ORDERING INFORMATION

#### 64-pin



\* 64-pin DIP not recommended for new designs

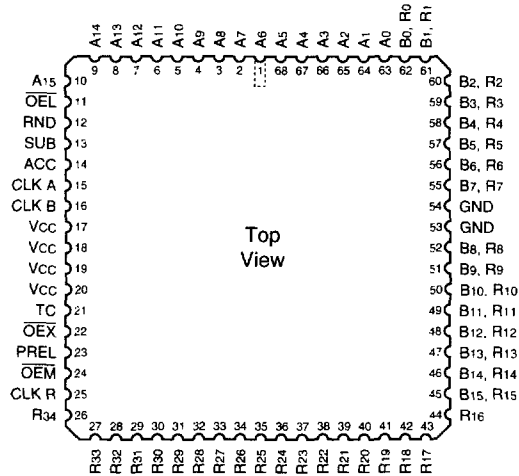
#### 68-pin



Speed	Sidebraze Hermetic DIP (D6)	Ceramic Pin Grid Array (G2)
<b>0°C to +70°C — COMMERCIAL SCREENING</b>		
65 ns	LMA1010DC65	LMA1010GC65
55 ns	LMA1010DC55	LMA1010GC55
45 ns	LMA1010DC45	LMA1010GC45
35 ns		LMA1010GC35
25 ns		LMA1010GC25
20 ns		LMA1010GC20
<b>-55°C to +125°C — COMMERCIAL SCREENING</b>		
75 ns	LMA1010DM75	LMA1010GM75
65 ns	LMA1010DM65	LMA1010GM65
55 ns	LMA1010DM55	LMA1010GM55
40 ns		LMA1010GM40
30 ns		LMA1010GM30
25 ns		LMA1010GM25
<b>-55°C to +125°C — MIL-STD-883 COMPLIANT</b>		
75 ns	LMA1010DMB75	LMA1010GMB75
65 ns	LMA1010DMB65	LMA1010GMB65
55 ns	LMA1010DMB55	LMA1010GMB55
40 ns		LMA1010GMB40
30 ns		LMA1010GMB30
25 ns		LMA1010GMB25

## LMA2010 — ORDERING INFORMATION

68-pin



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Speed	Plastic J-Lead Chip Carrier (J2)	Ceramic Leadless Chip Carrier (K3)		
<b>0°C to +70°C — COMMERCIAL SCREENING</b>				
65 ns	LMA2010JC65			
55 ns	LMA2010JC55			
45 ns	LMA2010JC45			
35 ns	LMA2010JC35			
25 ns	LMA2010JC25			
20 ns	LMA2010JC20			
<b>-55°C to +125°C — COMMERCIAL SCREENING</b>				
75 ns				
65 ns				
55 ns				
40 ns				
30 ns				
25 ns				
<b>-55°C to +125°C — MIL-STD-883 COMPLIANT</b>				
75 ns		LMA2010KMB75		
65 ns		LMA2010KMB65		
55 ns		LMA2010KMB55		
40 ns		LMA2010KMB40		
30 ns		LMA2010KMB30		
25 ns		LMA2010KMB25		